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1 Overview

The following section provides a high-level overview of the MPC8560 features. Figure 1 shows the major functional units within the MPC8560.

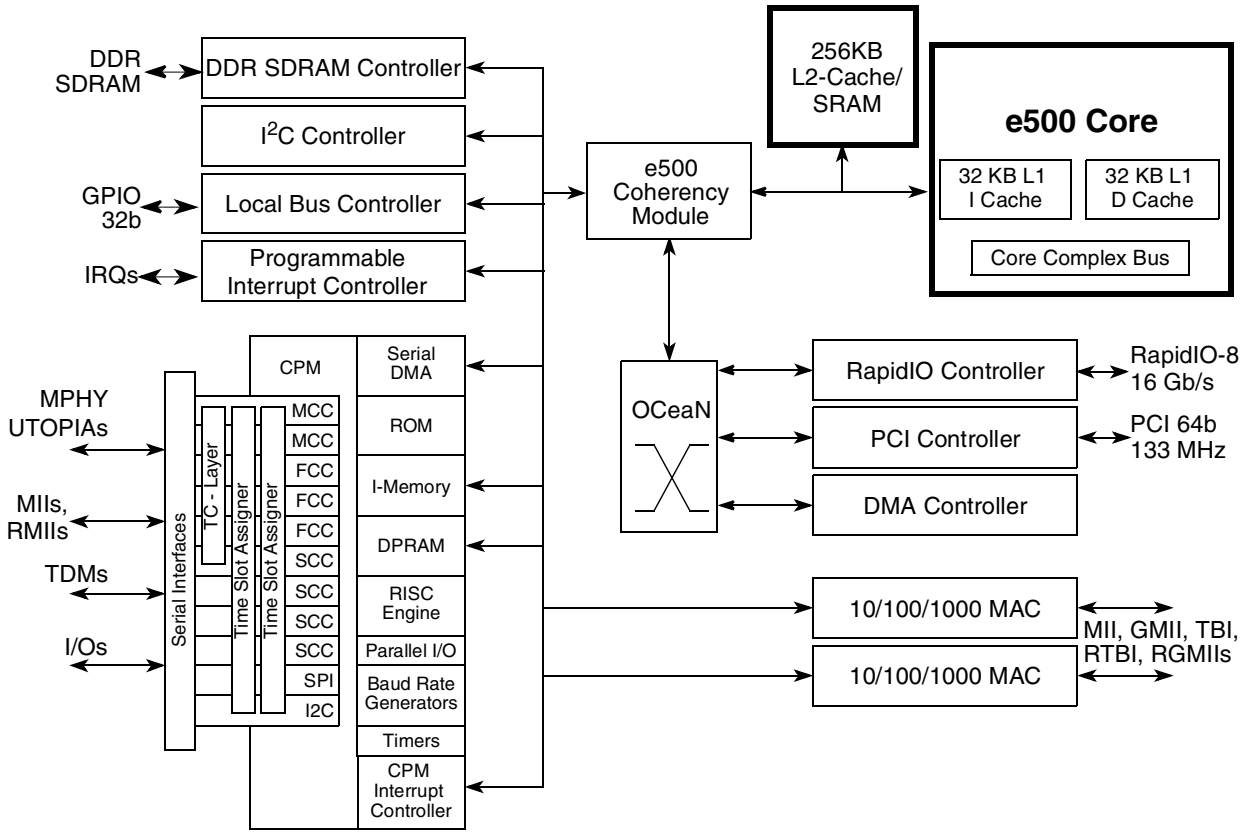


Figure 1. MPC8560 Block Diagram

1.1 Key Features

The following lists an overview of the MPC8560 feature set.

- High-performance, 32-bit Book E–enhanced core that implements the Power Architecture
  - 32-Kbyte L1 instruction cache and 32-Kbyte L1 data cache with parity protection. Caches can be locked entirely or on a per-line basis. Separate locking for instructions and data
  - Memory management unit (MMU) especially designed for embedded applications
  - Enhanced hardware and software debug support
  - Performance monitor facility (similar to but different from the MPC8560 performance monitor described in Chapter 18, “Performance Monitor.”
- High-performance RISC CPM operating at up to 333 MHz
  - CPM software compatibility with previous PowerQUICC families
  - One instruction per clock

  - Interrupts can be routed to the e500 core's standard or critical interrupt inputs
  - Interrupt summary registers allow fast identification of interrupt source
- I^2C controller
  - Two-wire interface
  - Multiple master support
  - Master or slave I^2C mode support
  - On-chip digital filtering rejects spikes on the bus
- Boot sequencer
  - Optionally loads configuration data from serial ROM at reset via the I^2C interface
  - Can be used to initialize configuration registers and/or memory
  - Supports extended I^2C addressing mode
  - Data integrity checked with preamble signature and CRC
- Local bus controller (LBC)
  - Multiplexed 32-bit address and data operating at up to 166 MHz
  - Eight chip selects support eight external slaves
  - Up to eight-beat burst transfers
  - The 32-, 16-, and 8-bit port sizes are controlled by an on-chip memory controller
  - Three protocol engines available on a per chip select basis:
    - General purpose chip select machine (GPCM)
    - Three user programmable machines (UPMs)
    - Dedicated single data rate SDRAM controller
  - Parity support
  - Default boot ROM chip select with configurable bus width (8-,16-, or 32-bit)
- Two three-speed (10/100/1Gb) Ethernet controllers (TSECs)
  - Dual IEEE 802.3, 802.3u, 802.3x, 802.3z, 802.3ac, 802.3ab compliant controllers
  - Support for different Ethernet physical interfaces:
    - 10/100/1Gb Mbps IEEE 802.3 GMII
    - 10/100 Mbps IEEE 802.3 MII
    - 10 Mbps IEEE 802.3 MII
    - 1000 Mbps IEEE 802.3z TBI
    - 10/100/1Gb Mbps RGMII/RTBI
  - Full- and half-duplex support
  - Buffer descriptors are backward compatible with MPC8260 and MPC860T 10/100 programming models
  - 9.6-Kbyte jumbo frame support
  - RMON statistics support
  - 2-Kbyte internal transmit and receive FIFOs

Table 1. Absolute Maximum Ratings [1] (continued)

Characteristic		Symbol	Max Value	Unit	Notes
DDR DRAM I/O voltage		GV_{DD}	–0.3 to 3.63	V	—
Three-speed Ethernet I/O voltage		LV_{DD}	–0.3 to 3.63 –0.3 to 2.75	V	—
CPM, PCI/PCI-X, local bus, RapidIO, 10/100 Ethernet,MII management, DUART, system control and power management, I^2C, and JTAG I/O voltage		OV_{DD}	–0.3 to 3.63	V	3
Input voltage	DDR DRAM signals	MV_{IN}	–0.3 to (GV_{DD} + 0.3)	V	2, 5
	DDR DRAM reference	MV_{REF}	–0.3 to (GV_{DD} + 0.3)	V	2, 5
	Three-speed Ethernet signals	LV_{IN}	–0.3 to (LV_{DD} + 0.3)	V	4, 5
	CPM, Local bus, RapidIO, 10/100 Ethernet, SYSCLK, system control and power management, I^2C, and JTAG signals	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	5
	PCI/PCI-X	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	6
Storage temperature range		T_{STG}	–55 to 150	°C	—

Notes:

1. Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
2. **Caution:** MV_{IN} must not exceed GV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
3. **Caution:** OV_{IN} must not exceed OV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
4. **Caution:** LV_{IN} must not exceed LV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
5. (M,L,O)V_{IN} and MV_{REF} may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 2.
6. OV_{IN} on the PCI interface may overshoot/undershoot according to the PCI Electrical Specification for 3.3-V operation, as shown in Figure 3.

2.1.2 Power Sequencing

The MPC8560 requires its power rails to be applied in a specific sequence in order to ensure proper device operation. These requirements are as follows for power up:

1. V_{DD}, AV_{DD}
2. GV_{DD}, LV_{DD}, OV_{DD} (I/O supplies)

Items on the same line have no ordering requirement with respect to one another. Items on separate lines must be ordered sequentially such that voltage rails on a previous step must reach 90 percent of their value before the voltage rails on the current step reach 10 percent of theirs.

Table 6. Estimated Typical I/O Power Consumption (continued)

Interface	Parameter	GV_{DD} (2.5 V)	OV_{DD} (3.3 V)	LV_{DD} (3.3 V)	LV_{DD} (2.5 V)	Units	Notes
TDMA or TDMB	Nibble mode	—	10	—	—	mW	7
	Per channel	—	5	—	—		

Notes:

1. GV_{DD}=2.5, ECC enabled, 66% bus utilization, 33% write cycles, 10pF load on data, 10pF load on address/command, 10pF load on clock
2. OV_{DD}=3.3, 30pF load per pin, 54% bus utilization, 33% write cycles
3. OV_{DD}=3.3, 25pF load per pin, 5pF load on clock, 40% bus utilization, 33% write cycles
4. V_{DD}=1.2, OV_{DD}=3.3
5. LVDD=2.5/3.3, 15pF load per pin, 25% bus utilization
6. Power dissipation for one TSEC only
7. OV_{DD}=3.3, 10pF load per pin, 50% bus utilization

4 Clock Timing

4.1 System Clock Timing

Table 7 provides the system clock (SYSCLK) AC timing specifications for the MPC8560.

Table 7. SYSCLK AC Timing Specifications

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
SYSCLK frequency	f_{SYSCLK}	—	—	166	MHz	1
SYSCLK cycle time	t_{SYSCLK}	6.0	—	—	ns	—
SYSCLK rise and fall time	t_{KH}, t_{KL}	0.6	1.0	1.2	ns	2
SYSCLK duty cycle	t_{KHKL}/t_{SYSCLK}	40	—	60	%	3
SYSCLK jitter	—	—	—	+/- 150	ps	4, 5

Notes:

1. **Caution:** The CCB to SYSCLK ratio and e500 core to CCB ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB frequency do not exceed their respective maximum or minimum operating frequencies. Refer to Section 15.2, "Platform/System PLL Ratio," and Section 15.3, "e500 Core PLL Ratio," for ratio settings.
2. Rise and fall times for SYSCLK are measured at 0.6 V and 2.7 V.
3. Timing is guaranteed by design and characterization.
4. This represents the total input jitter—short term and long term—and is guaranteed by design.
5. For spread spectrum clocking, guidelines are +/-1% of the input frequency with a maximum of 60 kHz of modulation regardless of the input frequency.

6 DDR SDRAM

This section describes the DC and AC electrical specifications for the DDR SDRAM interface of the MPC8560.

6.1 DDR SDRAM DC Electrical Characteristics

Table 13 provides the recommended operating conditions for the DDR SDRAM component(s) of the MPC8560.

Table 13. DDR SDRAM DC Electrical Characteristics

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.18$	$GV_{DD} + 0.3$	V	4
Input low voltage	V_{IL}	–0.3	$MV_{REF} - 0.18$	V	4
Output leakage current	I_{OZ}	–10	10	μA	5
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–15.2	—	mA	—
Output low current (V_{OUT} = 0.35 V)	I_{OL}	15.2	—	mA	—
MV_{REF} input leakage current	I_{VREF}	—	100	μA	—

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
4. V_{IH} can tolerate an overshoot of 1.2V over GV_{DD} for a pulse width of ≤3 ns, and the pulse width cannot be greater than t_{MCK}. V_{IL} can tolerate an undershoot of 1.2V below GND for a pulse width of ≤3 ns, and the pulse width cannot be greater than t_{MCK}.
5. Output leakage is measured with all outputs disabled, $0 V \le V_{OUT} \le GV_{DD}$.

Table 14 provides the DDR capacitance.

Table 14. DDR SDRAM Capacitance

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, MSYNC_IN	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak to peak) = 0.2 V.

7.2.3.2 TBI Receive AC Timing Specifications

Table 26 provides the TBI receive AC timing specifications.

Table 26. TBI Receive AC Timing Specifications

At recommended operating conditions with LV_{DD} of 3.3 V ± 5%, or LV_{DD}=2.5V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
RX_CLK clock period	t_{TRX}		16.0		ns
RX_CLK skew	t_{SKTRX}	7.5	—	8.5	ns
RX_CLK duty cycle	t_{TRXH}/t_{TRX}	40	—	60	%
RCG[9:0] setup time to rising RX_CLK	t_{TRDVKH}	2.5	—	—	ns
RCG[9:0] hold time to rising RX_CLK	t_{TRDXKH}	1.5	—	—	ns
RX_CLK clock rise time and fall time	t_{TRXR}, t_{TRXF} [2,3]	0.7	—	2.4	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{TRDVKH} symbolizes TBI receive timing (TR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{TRX} clock reference (K) going to the high (H) state or setup time. Also, t_{TRDXKH} symbolizes TBI receive timing (TR) with respect to the time data input signals (D) went invalid (X) relative to the t_{TRX} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{TRX} represents the TBI (T) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall). For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (TRX).
2. Signal timings are measured at 0.7 V and 1.9 V voltage levels.
3. Guaranteed by design.

Figure 13 shows the TBI receive AC timing diagram.

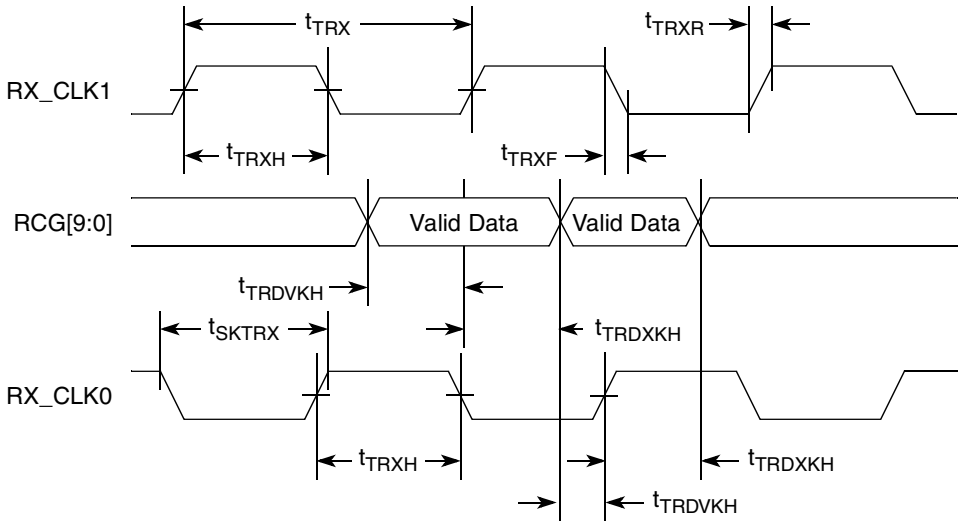


Figure 13. TBI Receive AC Timing Diagram

7.2.4 RGMII and RTBI AC Timing Specifications

Table 27 presents the RGMII and RTBI AC timing specifications.

Table 27. RGMII and RTBI AC Timing Specifications

At recommended operating conditions with LV_{DD} of 2.5 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
Data to clock output skew (at transmitter)	t_{SKRGT} [5]	–500	0	500	ps
Data to clock input skew (at receiver) [2]	t_{SKRGT}	1.0	—	2.8	ns
Clock period[3]	t_{RGT} [6]	7.2	8.0	8.8	ns
Duty cycle for 1000Base-T [4]	t_{RGTH}/t_{RGT} [6]	45	50	55	%
Duty cycle for 10BASE-T and 100BASE-TX [3]	t_{RGTH}/t_{RGT} [6]	40	50	60	%
Rise and fall time	t_{RGTR}, t_{RGTF} [6,7]	—	—	0.75	ns

Notes:

1. Note that, in general, the clock reference symbol representation for this section is based on the symbols RGT to represent RGMII and RTBI timing. For example, the subscript of t_{RGT} represents the TBI (T) receive (RX) clock. Note also that the notation for rise (R) and fall (F) times follows the clock symbol that is being represented. For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (RGT).
2. The RGMII specification requires that PC board designer add 1.5 ns or greater in trace delay to the RX_CLK in order to meet this specification. However, as stated above, this device will function with only 1.0 ns of delay.
3. For 10 and 100 Mbps, t_{RGT} scales to 400 ns ± 40 ns and 40 ns ± 4 ns, respectively.
4. Duty cycle may be stretched/shrunk during speed changes or while transitioning to a received packet's clock domains as long as the minimum duty cycle is not violated and stretching occurs for no more than three t_{RGT} of the lowest speed transitioned between.
5. Guaranteed by characterization.
6. Guaranteed by design.
7. Signal timings are measured at 0.5 V and 2.0 V voltage levels.

Table 28. MII Management DC Electrical Characteristics (continued)

Parameter	Symbol	Min	Max	Unit
Input high current (OV_{DD} = Max, V_{IN} [1] = 2.1 V)	I_{IH}	—	40	μA
Input low current (OV_{DD} = Max, V_{IN} = 0.5 V)	I_{IL}	–600	—	μA

Note:

1.Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

7.3.2 MII Management AC Electrical Specifications

Table 29 provides the MII management AC timing specifications.

Table 29. MII Management AC Timing Specifications

At recommended operating conditions with OV_{DD} is 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit	Notes
MDC frequency	f_{MDC}	0.893	—	10.4	MHz	2, 4
MDC period	t_{MDC}	96	—	1120	ns	
MDC clock pulse width high	t_{MDCH}	32	—	—	ns	
MDC to MDIO valid	t_{MDKHDV}			$2*[1/(f_{ccb\_clk}/8)]$	ns	3
MDC to MDIO delay	t_{MDKHDX}	10	—	$2*[1/(f_{ccb\_clk}/8)]$	ns	3
MDIO to MDC setup time	t_{MDDVKH}	5	—	—	ns	
MDIO to MDC hold time	t_{MDDXKH}	0	—	—	ns	
MDC rise time	t_{MDCR}	—	—	10	ns	4
MDC fall time	t_{MDHF}	—	—	10	ns	4

Notes:

1.The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, t_{MDDVKH} symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

2.This parameter is dependent on the CCB clock speed (that is, for a CCB clock of 267 MHz, the maximum frequency is 8.3 MHz and the minimum frequency is 1.2 MHz; for a CCB clock of 333 MHz, the maximum frequency is 10.4 MHz and the minimum frequency is 1.5 MHz).

3.This parameter is dependent on the CCB clock speed (that is, for a CCB clock of 267 MHz, the delay is 60 ns and for a CCB clock of 333 MHz, the delay is 48 ns).

4.Guaranteed by design.

Table 33. CPM DC Electrical Characteristics (continued)

Characteristic	Symbol	Min	Max	Unit	Notes
Output high voltage (I_{OH} = –2.0 mA)	V_{OH}	2.4	—	V	1
Output low voltage (I_{OL} = 3.2 mA)	V_{OL}	—	0.4	V	1

Note:
1. This specification applies to the following pins: PA[0–31], PB[4–31], PC[0–31], and PD[4–31].
2. V_{IL}(max) for the IIC interface is 0.8 V rather than the 1.5 V specified in the IIC standard

9.2 CPM AC Timing Specifications

Table 34 and Table 35 provide the CPM input and output AC timing specifications, respectively.

NOTE: Rise/Fall Time on CPM Input Pins

It is recommended that the rise/fall time on CPM input pins should not exceed 5 ns. This should be enforced especially on clock signals. Rise time refers to signal transitions from 10% to 90% of VCC; fall time refers to transitions from 90% to 10% of VCC.

Table 34. CPM Input AC Timing Specifications [1]

Characteristic	Symbol [2]	Min [3]	Unit
FCC inputs—internal clock (NMSI) input setup time	t_{FIIVKH}	6	ns
FCC inputs—internal clock (NMSI) hold time	t_{FIIXKH}	0	ns
FCC inputs—external clock (NMSI) input setup time	t_{FEIVKH}	2.5	ns
FCC inputs—external clock (NMSI) hold time	t_{FEIXKH}b	2	ns
SCC/SPI inputs—internal clock (NMSI) input setup time	t_{NIIVKH}	6	ns
SCC/SPI inputs—internal clock (NMSI) input hold time	t_{NIIXKH}	0	ns
SCC/SPI inputs—external clock (NMSI) input setup time	t_{NEIVKH}	4	ns
SCC/SPI inputs—external clock (NMSI) input hold time	t_{NEIXKH}	2	ns
TDM inputs/SI—input setup time	t_{TDIVKH}	4	ns
TDM inputs/SI—hold time	t_{TDIXKH}	3	ns

Figure 35 provides the test access port timing diagram.

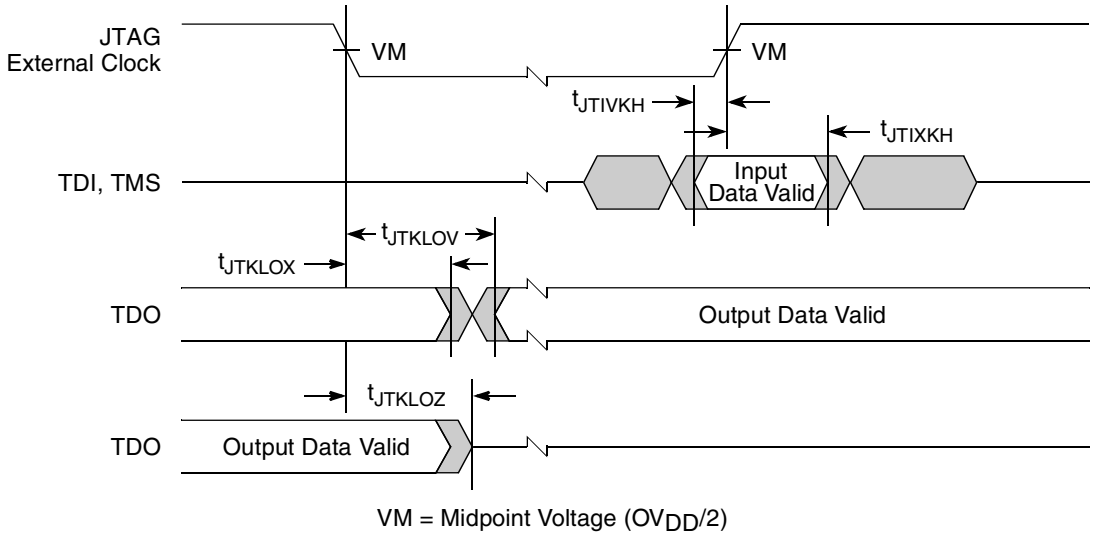


Figure 35. Test Access Port Timing Diagram

11 I²C

This section describes the DC and AC electrical characteristics for the I²C interface of the MPC8560.

11.1 I²C DC Electrical Characteristics

Table 40 provides the DC electrical characteristics for the I²C interface of the MPC8560.

Table 40. I²C DC Electrical Characteristics

At recommended operating conditions with OV_{DD} of 3.3 V ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
Input high voltage level	V_{IH}	$0.7 \times OV_{DD}$	OV_{DD}+ 0.3	V	—
Input low voltage level	V_{IL}	–0.3	$0.3 \times OV_{DD}$	V	—
Low level output voltage	V_{OL}	0	$0.2 \times OV_{DD}$	V	1
Pulse width of spikes which must be suppressed by the input filter	t_{I2KHKL}	0	50	ns	2
Input current each I/O pin (input voltage is between $0.1 \times OV_{DD}$ and $0.9 \times OV_{DD}$(max)	I_I	–10	10	μA	3
Capacitance for each I/O pin	C_I	—	10	pF	—

Notes:

1. Output voltage (open drain or open collector) condition = 3 mA sink current.
2. Refer to the *MPC8560 PowerQUICC III Integrated Communications Processor Preliminary Reference Manual* for information on the digital filter used.
3. I/O pins will obstruct the SDA and SCL lines if OV_{DD} is switched off.

Figure 37 shows the AC timing diagram for the I^2C bus.

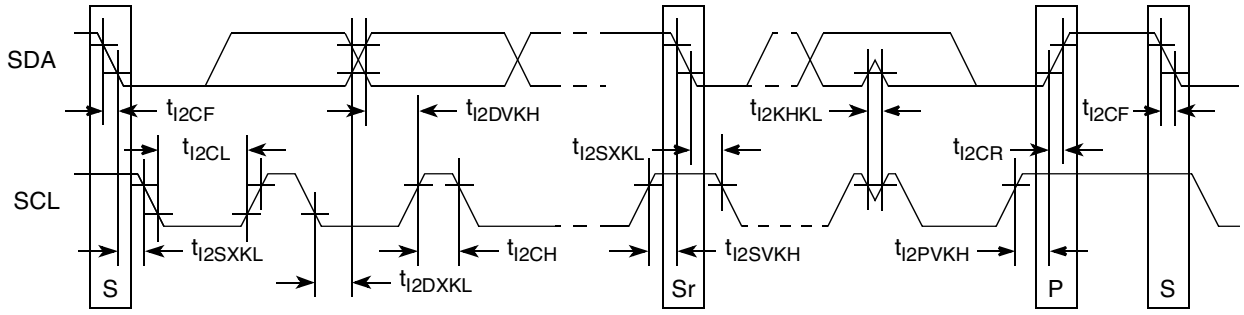


Figure 37. I^2C Bus AC Timing Diagram

12 PCI/PCI-X

This section describes the DC and AC electrical specifications for the PCI/PCI-X bus of the MPC8560.

12.1 PCI/PCI-X DC Electrical Characteristics

Table 42 provides the DC electrical characteristics for the PCI/PCI-X interface of the MPC8560.

Table 42. PCI/PCI-X DC Electrical Characteristics [1]

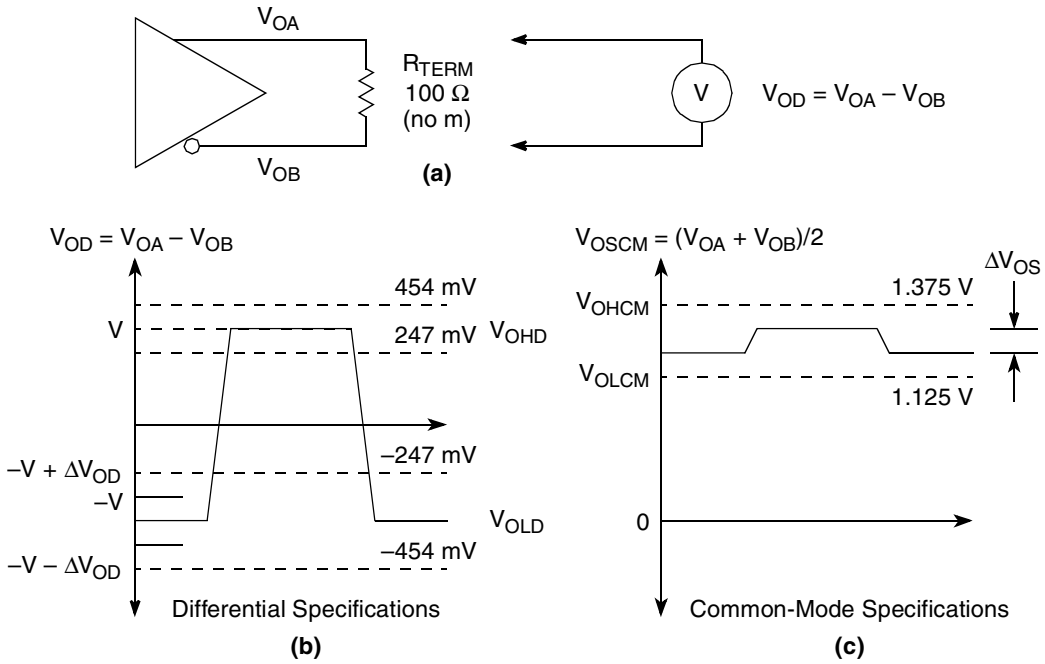
Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (V_{IN} [2] = 0 V or V_{IN} = V_{DD})	I_{IN}	—	±5	μA
High-level output voltage (OV_{DD} = min, I_{OH} = –100 μA)	V_{OH}	OV_{DD} – 0.2	—	V
Low-level output voltage (OV_{DD} = min, I_{OL} = 100 μA)	V_{OL}	—	0.2	V

Notes:

1.Ranges listed do not meet the full range of the DC specifications of the *PCI 2.2 Local Bus Specifications*.

2.Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

Figure 41 shows the DC driver signal levels.



Note: V_{OA} refers to voltage at output A; V_{OB} refers to voltage at output B.

Figure 41. DC Driver Signal Levels

13.2 RapidIO AC Electrical Specifications

This section contains the AC electrical specifications for a RapidIO 8/16 LP-LVDS device. The interface defined is a parallel differential low-power high-speed signal interface. Note that the source of the transmit clock on the RapidIO interface is dependent on the settings of the LGPL[0:1] signals at reset. Note that the default setting makes the core complex bus (CCB) clock the source of the transmit clock. See Chapter 4 of the Reference Manual for more details on reset configuration settings.

13.3 RapidIO Concepts and Definitions

This section specifies signals using differential voltages. Figure 42 shows how the signals are defined. The figure shows waveforms for either a transmitter output (TD and $\overline{\text{TD}}$) or a receiver input (RD and $\overline{\text{RD}}$). Each signal swings between A volts and B volts where A > B. Using these waveforms, the definitions are as follows:

- The transmitter output and receiver input signals TD, $\overline{\text{TD}}$, RD, and $\overline{\text{RD}}$ each have a peak-to-peak swing of A-B volts.
- The differential output signal of the transmitter, V_{OD}, is defined as $V_{TD} - V_{\overline{TD}}$.
- The differential input signal of the receiver, V_{ID}, is defined as $V_{RD} - V_{\overline{RD}}$.
- The differential output signal of the transmitter or input signal of the receiver, ranges from A – B volts to – (A – B) volts.

Table 48. RapidIO Driver AC Timing Specifications—500 Mbps Data Rate (continued)

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Duty cycle	DC	48	52	%	2, 6
V_{OD} rise time, 20%–80% of peak-to-peak differential signal swing	t_{FALL}	200	—	ps	3, 6
V_{OD} fall time, 20%–80% of peak-to-peak differential signal swing	t_{RISE}	200	—	ps	6
Data valid	DV	1260	—	ps	
Skew of any two data outputs	t_{DPAIR}	—	180	ps	4, 6
Skew of single data outputs to associated clock	$t_{SKEW,PAIR}$	–180	180	ps	5, 6

Notes:

1.See Figure 44.

2.Requires ±100 ppm long term frequency stability.

3.Measured at V_{OD} = 0 V.

4.Measured using the RapidIO transmit mask shown in Figure 44.

5.See Figure 49.

6.Guaranteed by design.

Table 49. RapidIO Driver AC Timing Specifications—750 Mbps Data Rate

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Differential output high voltage	V_{OHD}	200	540	mV	1
Differential output low voltage	V_{OLD}	–540	–200	mV	1
Duty cycle	DC	48	52	%	2, 6
V_{OD} rise time, 20%–80% of peak-to-peak differential signal swing	t_{FALL}	133	—	ps	3, 6
V_{OD} fall time, 20%–80% of peak-to-peak differential signal swing	t_{RISE}	133	—	ps	6
Data valid	DV	800	—	ps	6
Skew of any two data outputs	t_{DPAIR}	—	133	ps	4, 6
Skew of single data outputs to associated clock	$t_{SKEW,PAIR}$	–133	133	ps	5, 6

Notes:

1.See Figure 44.

2.Requires ±100 ppm long term frequency stability.

3.Measured at V_{OD} = 0 V.

4.Measured using the RapidIO transmit mask shown in Figure 44.

5.See Figure 49.

6.Guaranteed by design.

Table 54. MPC8560 Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
JTAG				
TCK	AF21	I	OV_{DD}	—
TDI	AG21	I	OV_{DD}	12
TDO	AF19	O	OV_{DD}	11
TMS	AF23	I	OV_{DD}	12
$\overline{\text{TRST}}$	AG23	I	OV_{DD}	12
DFT				
$\overline{\text{LSSD\_MODE}}$	AG19	I	OV_{DD}	21
L1_TSTCLK	AB22	I	OV_{DD}	21
L2_TSTCLK	AG22	I	OV_{DD}	21
$\overline{\text{TEST\_SEL}}$	AH20	I	OV_{DD}	3
Thermal Management				
THERM0	AG2	I	—	14
THERM1	AH3	I	—	14
Power Management				
ASLEEP	AG18	I/O		9, 19
Power and Ground Signals				
$AV_{DD}1$	AH19	Power for e500 PLL (1.2 V)	$AV_{DD}1$	—
$AV_{DD}2$	AH18	Power for CCB PLL (1.2 V)	$AV_{DD}2$	—
$AV_{DD}3$	AH17	Power for CPM PLL (1.2 V)	$AV_{DD}3$	—
GND	A12, A17, B3, B14, B20, B26, B27, C2, C4, C11,C17, C19, C22, C27, D8, E3, E12, E24, F11, F18, F23, G9, G12, G25, H4, H12, H14, H17, H20, H22, H27, J19, J24, K5, K9, K18, K23, K28, L6, L20, L25, M4, M12, M14, M16, M22, M27, N2, N13, N15, N17, P12, P14, P16, P23, R13, R15, R17, R20, R26, T3, T8, T10, T12, T14, T16, U6, U13, U15, U16, U17, U21, V7, V10, V26, W5, W18, W23, Y8, Y16, AA6, AA13, AB4, AB11, AB19, AC6, AC9, AD3, AD8, AD17, AF2, AF4, AF10, AF13, AF15, AF27, AG3, AG7, AG26	—	—	—
GV_{DD}	A14, A20, A25, A26, A27, A28, B17, B22, B28, C12, C28, D16, D19, D21, D24, D28, E17, E22, F12, F15, F19, F25, G13, G18, G20, G23, G28, H19, H24, J12, J17, J22, J27, K15, K20, K25, L13, L23, L28, M25, N21	Power for DDR DRAM I/O Voltage (2.5 V)	GV_{DD}	—

Conductivity	Value	Unit
Lid (12 × 14 × 1 mm)		
k_x	360	W/(m × K)
k_y	360	
k_z	360	
Lid Adhesive—Collapsed resistance (10 × 12 × 0.050 mm)		
k_x	1	
k_y	1	
k_z	1	
Die (10 × 12 × 0.76 mm)		
Bump/Underfill—Collapsed resistance (10 × 12 × 0.070 mm)		
k_x	0.6	
k_y	0.6	
k_z	1.9	
Substrate and Solder Balls (29 × 29 × 1.47 mm)		
k_x	10.2	
k_y	10.2	
k_z	1.6	

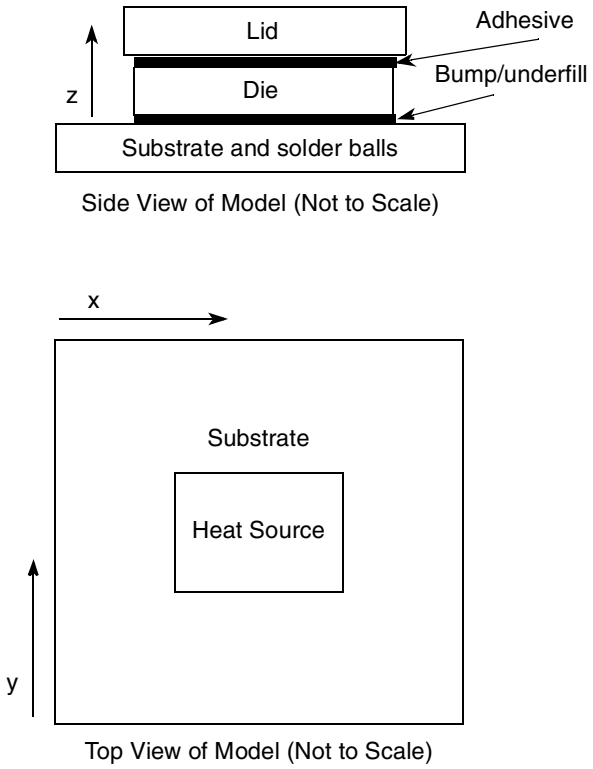


Figure 52. MPC8560 Thermal Model

16.2.2 Internal Package Conduction Resistance

For the packaging technology, shown in Table 60, the intrinsic internal conduction thermal resistance paths are as follows:

- The die junction-to-case thermal resistance
- The die junction-to-board thermal resistance

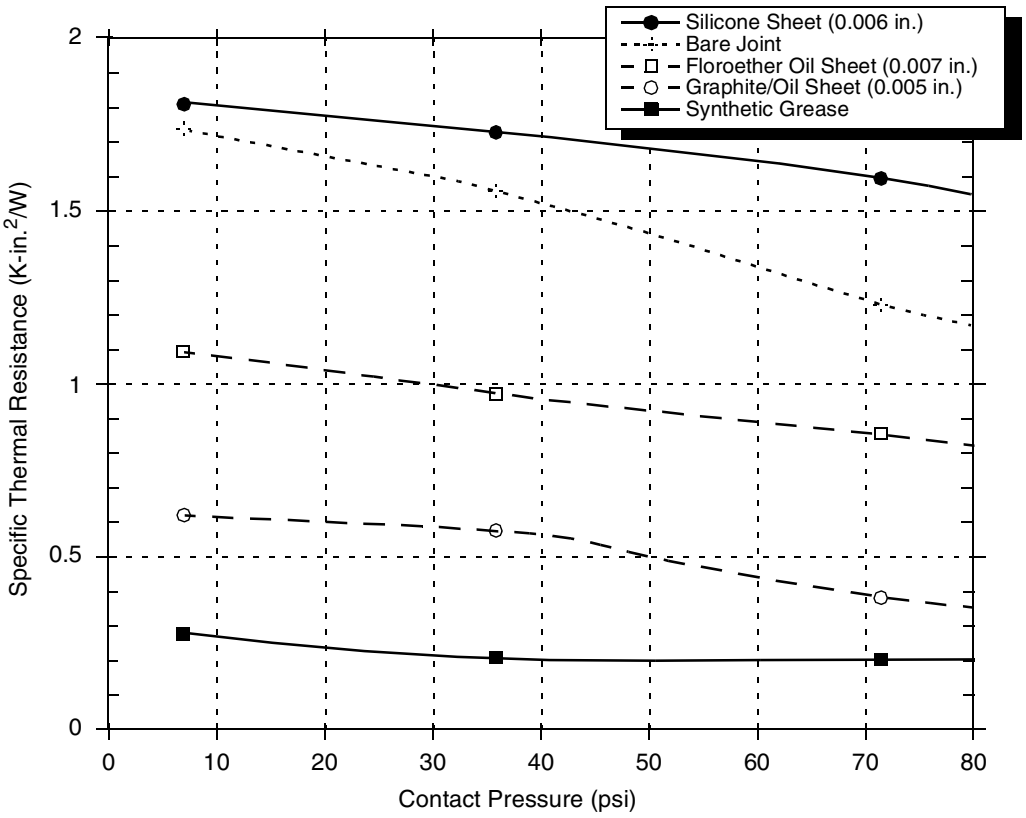


Figure 54. Thermal Performance of Select Thermal Interface Materials

The system board designer can choose between several types of thermal interface. There are several commercially-available thermal interfaces provided by the following vendors:

Chomerics, Inc. 77 Dragon Ct. Woburn, MA 01888-4014 Internet: www.chomerics.com	781-935-4850
Dow-Corning Corporation Dow-Corning Electronic Materials 2200 W. Salzburg Rd. Midland, MI 48686-0997 Internet: www.dowcorning.com	800-248-2481
Shin-Etsu MicroSi, Inc. 10028 S. 51st St. Phoenix, AZ 85044 Internet: www.microsi.com	888-642-7674
The Bergquist Company 18930 West 78th St. Chanhassen, MN 55317 Internet: www.bergquistcompany.com	800-347-4572

The spring mounting should be designed to apply the force only directly above the die. By localizing the force, rocking of the heat sink is minimized. One suggested mounting method attaches a plastic fence to the board to provide the structure on which the heat sink spring clips. The plastic fence also provides the opportunity to minimize the holes in the printed-circuit board and to locate them at the corners of the package. Figure 56 and Figure 57 provide exploded views of the plastic fence, heat sink, and spring clip.

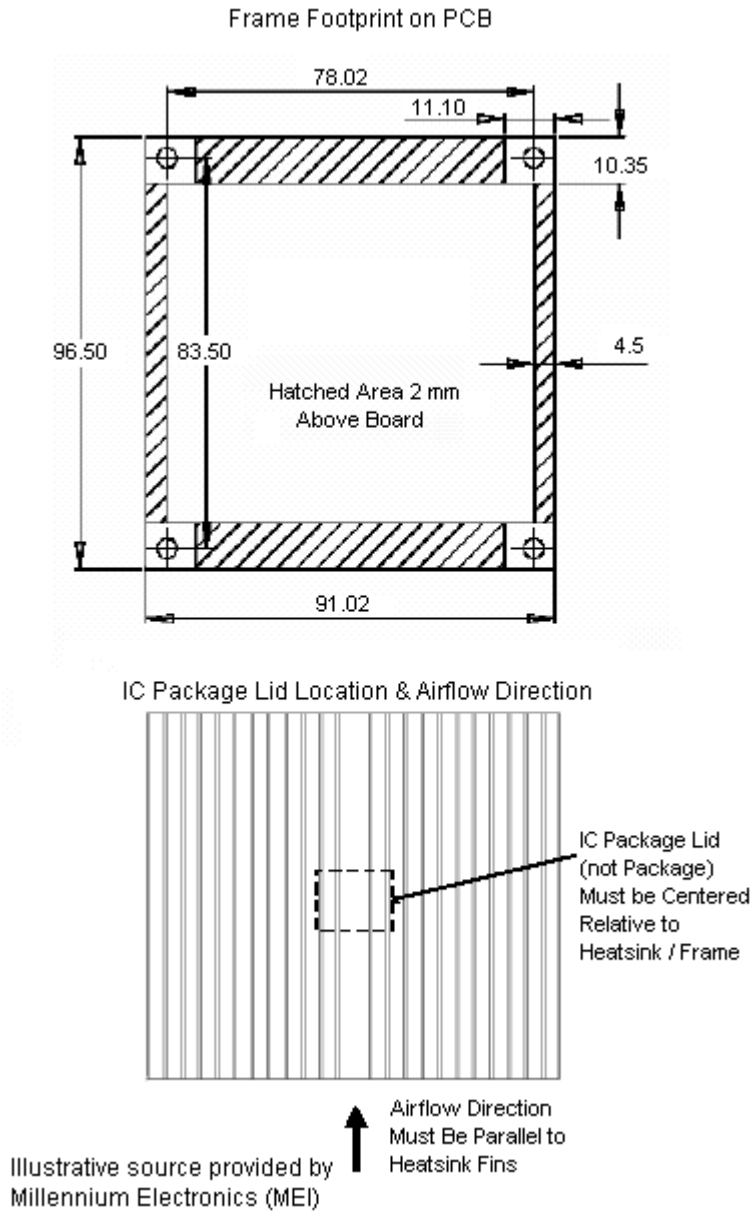
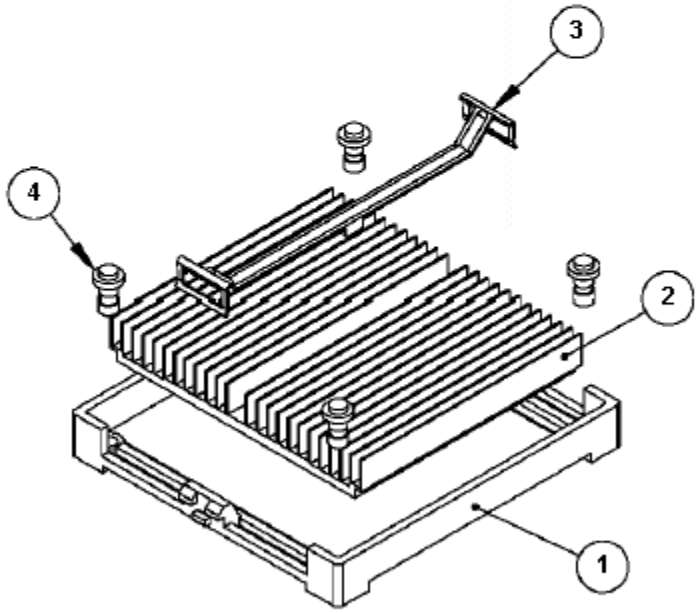


Figure 56. Exploded Views (1) of a Heat Sink Attachment using a Plastic Force

Item No	QTY	MEI PN	Description
1	1	MFRAME-2000	HEATSINK FRAME
2	1	MSNK-1120	EXTRUDED HEATSINK
3	1	MCLIP-1013	CLIP
4	4	MPPINS-1000	FRAME ATTACHMENT PINS



Illustrative source provided by
Millennium Electronics (MEI)

Figure 57. Exploded Views (2) of a Heat Sink Attachment using a Plastic Fence

The die junction-to-ambient and the heat sink-to-ambient thermal resistances are common figure-of-merits used for comparing the thermal performance of various microelectronic packaging technologies, one should exercise caution when only using this metric in determining thermal management because no single parameter can adequately describe three-dimensional heat flow. The final die-junction operating temperature is not only a function of the component-level thermal resistance, but the system level design and its operating conditions. In addition to the component's power consumption, a number of factors affect the final operating die-junction temperature: airflow, board population (local heat flux of adjacent components), system air temperature rise, altitude, etc.

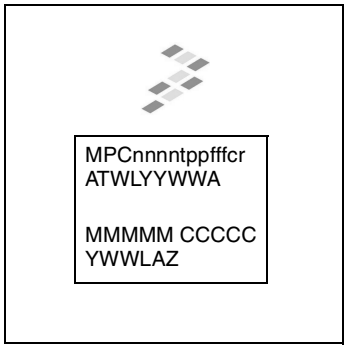
Due to the complexity and the many variations of system-level boundary conditions for today's microelectronic equipment, the combined effects of the heat transfer mechanisms (radiation convection and conduction) may vary widely. For these reasons, we recommend using conjugate heat transfer models for the boards, as well as, system-level designs.

Table 62. Document Revision History (continued)

Rev. No.	Substantive Change(s)
1.2	Section 1.1.1—Updated feature list. Section 1.2.1.1—Updated notes for Table 1. Section 1.2.1.2—Removed 5-V PCI interface overshoot and undershoot figure. Section 1.2.1.3—Added this section to summarize impedance driver settings for various interfaces. Section 1.4—Updated rows in Reset Initialization timing specifications table. Added a table with DLL and PLL timing specifications. Section 1.5.2.2—Updated note 6 of DDR SDRAM Output AC Timing Specifications table. Section 1.7—Changed the minimum input low current from -600 to -15 μA for the RGMII DC electrical characteristics. Section 1.7.2—Changed LCS[3:4] to TSEC1_TXD[6:5]. Updated notes regarding LCS[3:4]. Section 1.13.2—Updated the mechanical dimensions diagram for the package. Section 1.13.3—Updated the notes for LBCTL, TRIG_OUT, and ASLEEP. Corrected pin assignments for IIC_SDA and IIC_SCL. Corrected reserved pin assignment of V11 to U11. V11 is actually $\overline{\text{PCI\_STOP}}$. Section 1.14.1—Updated the table for frequency options with respect to platform/CCB frequencies. Section 1.14.4—Edited Frequency options with respect to memory bus speeds.
1.1	Made updates throughout document. Section 1.6.1—Added symbols and note for the GTX_CLK125 timing parameters. Section 1.11.3—Updated pin list table: LGPL5/LSDAMUX to LGPL5, LA[27:29] and LA[30:31] to LA[27:31], TRST to $\overline{\text{TRST}}$, added GBE Clocking section and EC_GTX_CLK125 signal. Figure 50—Updated pin 2 connection information.
1	Original Customer Version.

19.2 Part Marking

Parts are marked as the example shown in Figure 62.



FC-PBGA

Notes:

MMMMM is the 5-digit mask number.
ATWLYYWWA is the traceability code.
CCCCC is the country of assembly. This space is left blank if parts are assembled in the United States.
YWWLAZ is the assembly traceability code.

Figure 62. Part Marking for FC-PBGA Device